DAC500N170PX3

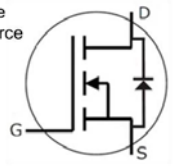
Silicon Carbide Enhancement Mode MOSFET

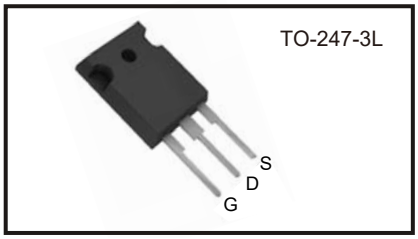
V_{DSS}	1700V
$I_{D(@25℃)}$	7.3A
$R_{DS(ON)\ typ.}$	500mΩ

Features

- High blocking voltage with low Rds(on)
- High frequency operation with low Capacitance
- Simple to drive and easy to parallel
- Robust body diode with low Qrr
- 100% Avalanche Tested

D : Drain
G : Gate
S : Source





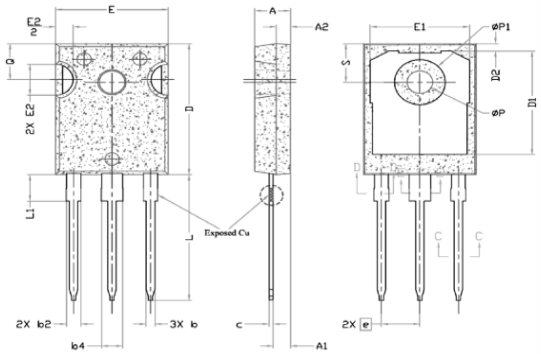
Benefits

- Superior robustness and system reliability
- Higher system efficiency
- Easier paralleling without thermal runaway
- Capable of high temperature application
- Faster and more efficient switching

Applications

- EV motor drives
- EV/HEV charging station
- Energy storage and Battery charging
- High voltage DC-DC converters
- Solar / Wind Inverters
- UPS and PFC

Package Dimensions



Absolute Maximum Ratings

(Tc = 25℃ unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage	V_{GS}=0V I_D=100μA	V_{DS}	1700	V
Gate-Source Voltage (dynamic)	AC (f>1 Hz, duty cycle<1%, pulse width<200ns)	V_{GS}	-10/+25	V
Gate-Source Voltage (static)		$V_{GS(op)}$	-5/+20	V
Drain Current-Continuous	V_{GS}=20V@ T_C=25°C V_{GS}=20V@ T_C=100°C	I_D	7.3 5	A
Pulse Drain Current		$I_{D,pulse}$	14	A
Power Dissipation		P_D	83	W
Storage Temperature Range		T_{STG}	-55 to +175	°C
Operating Junction Temperature Range		T_J	-55 to +175	°C
Soldering Temperature		T_L	260	°C
Avalanche Capability, single pulse *	V_{DD}=100V V_{GS}=10V L=2mH	I_{AV}	12	A
Avalanche Capability, single pulse**	V_{DD}=100V V_{GS}=10V L=2mH	E_{AV}	120	mJ

* 100% tested in 63% rating
** 100% tested in 40% rating

SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.50	2.00	2.49	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
c	0.55	0.60	0.69	6
c1	0.55	0.60	0.65	
D	20.80	20.95	21.10	4
D1	16.25	16.55	17.65	5
D2	0.51	1.19	1.35	
E	15.75	15.94	16.13	4
E1	13.46	14.02	14.16	5
E2	4.32	4.91	5.49	3
e	5.44BSC			
L	19.81	20.07	20.32	
L1	4.10	4.19	4.40	6
øP	3.56	3.61	3.65	7
øP1	7.19REF.			
Q	5.39	5.79	6.20	
S	6.04	6.17	6.30	

Electrical Characteristics @ T_C =25°C (unless otherwise specified)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Unit
OFF Characteristics							
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V，I_D =0.1mA		1700	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =1700V V_{GS} =0V	T_J =25℃	-	0.5	60	μA
			T_J =175℃	-	10	-	
Gate-Source Leakage Current	I_{GSS}	V_{GS} =20V，V_{DS} =0V		-	5	100	nA
		V_{GS} =-5V，V_{DS} =0V		-100	-5	-	
ON Characteristics							
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}，I_D =1mA	T_J =25℃	2.0	2.9	4.0	V
			T_J =175℃	-	2.0	-	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} =20V，I_D =2A	T_J =25℃	-	500	700	mΩ
			T_J =175℃	-	1120	-	
Transconductance	g_{fs}	V_{DS} =20V，I_D =2A	T_J =25℃	-	1.3	-	S
			T_J =175℃	-	1.3	-	
Internal Gate Resistance	$R_{G(int.)}$	f =1MHz，I_D =0A		-	5.8	-	Ω
Dynamic Characteristics							
Input Capacitance	C_{iss}	V_{DS} =1200V V_{GS} =0V f =1MHz V_{AC} =25mV		-	220	-	pF
Output Capacitance	C_{oss}			-	13	-	
Reverse Transfer Capacitance	C_{rss}			-	2	-	
Coss Stored Energy	E_{oss}			-	10	-	μJ
Turn-On Switching Energy	E_{on}	V_{DS} =1200V，V_{GS} =-5/+20V I_D =2A，$R_{G(ext)}$ =2.0Ω L=1000μH		-	98	-	μJ
Turn-Off Switching Energy	E_{off}			-	40	-	
Switching Characteristics							
Turn-On Delay Time	$t_{d(on)}$	V_{DS} =1200V，V_{GS} =-5/+20V I_D =2A，$R_{G(ext)}$ =2.0Ω L=1000μH		-	5	-	ns
Rise Time	t_r			-	15	-	
Turn-Off Delay Time	$t_{d(off)}$			-	23	-	
Fall Time	t_f			-	65	-	
Total Gate Charge	Q_g	V_{DS} =1200V V_{GS} =-5/+20V I_D =2A		-	20	-	nC
Gate to Source Charge	Q_{gs}			-	3	-	
Gate to Drain Charge	Q_{gd}			-	11	-	
Body Diode Characteristics							
Inverse Diode Forward Voltage	V_{SD}	V_{GS}=-5V，I_{SD}=1A	T_J =25℃	-	3.9	-	V
Inverse Diode Forward Voltage			T_J =175℃	-	3.4	-	V
Continuous Diode Forward Current	I_S	V_{GS}=-5V，T_J =25°C		-	-	7	A
Reverse Recovery Time	T_{rr}	I_{SD}=2A ，V_{GS}=-5V V_R=1200V dif/dt=3250A/μs		-	5	-	ns
Reverse Recovery Charge	Q_{rr}			-	30	-	nC
Peak Reverse Recovery Current	I_{rrm}			-	10	-	A
Thermal Resistance							
Thermal Resistance, Junction-to-Case	$R\theta_{JC}$			-	1.4	1.8	°C/W

Typical Performance

Fig 1. Output Characteristics, T_J = -55°C

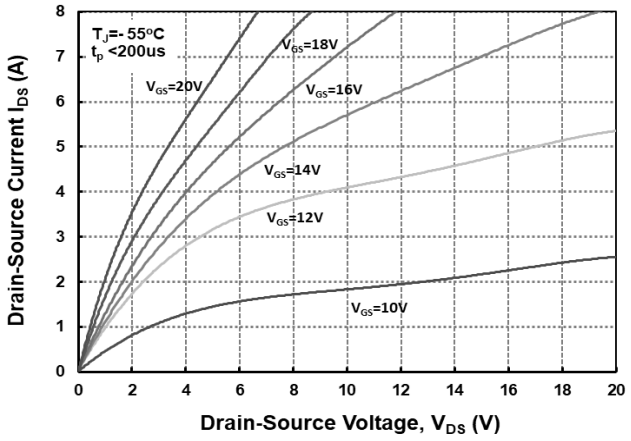


Fig 2. Output Characteristics, T_J = 25°C

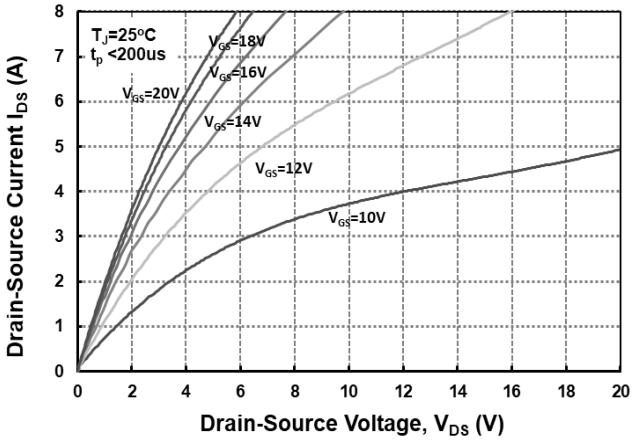


Fig 3. Output Characteristics, T_J = 175°C

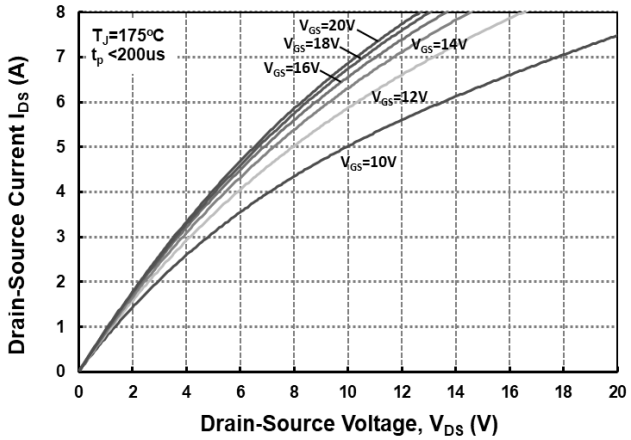


Fig 4. Normalized On-Resistance vs. Temperature

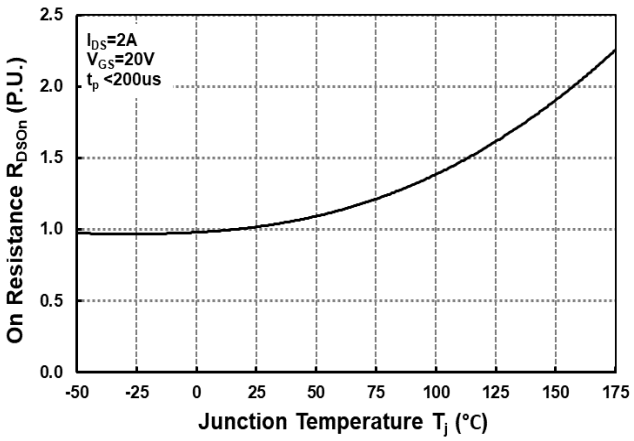


Fig 5. On-Resistance vs. Drain Current for Various Temperatures

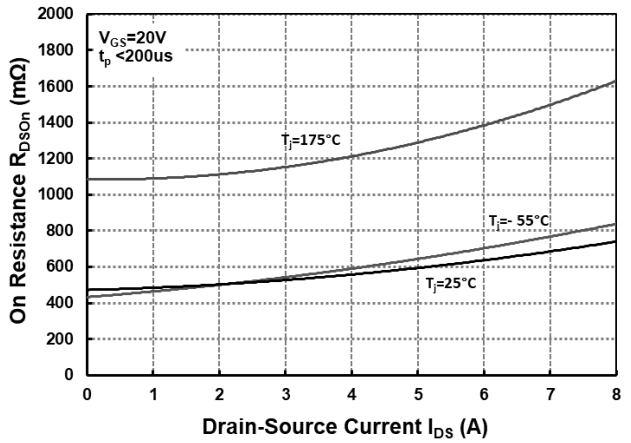
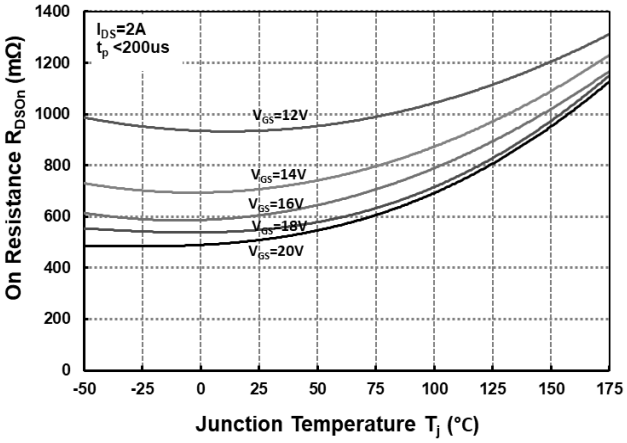


Fig 6. On-Resistance vs. Temperature for Various Gate Voltage



Typical Performance

Fig 7. Transfer Characteristic for Various Junction Temperatures

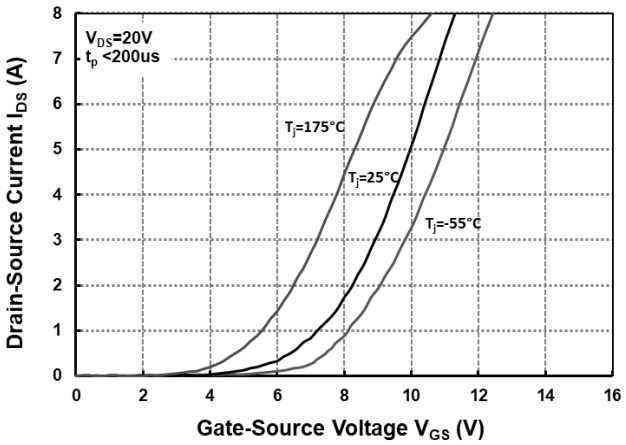


Fig 8. Body Diode Characteristics @ -55°C

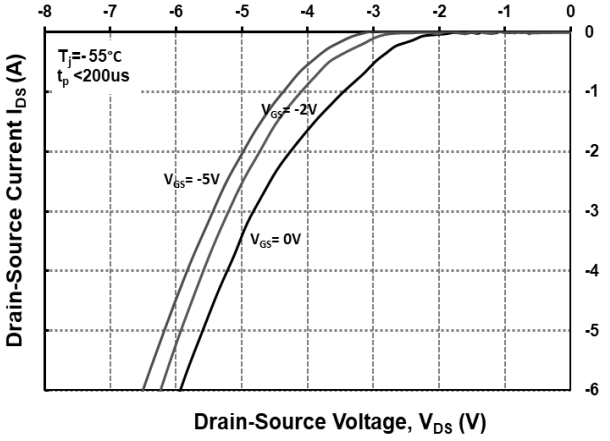


Fig 9. Body Diode Characterisics @ 25°C

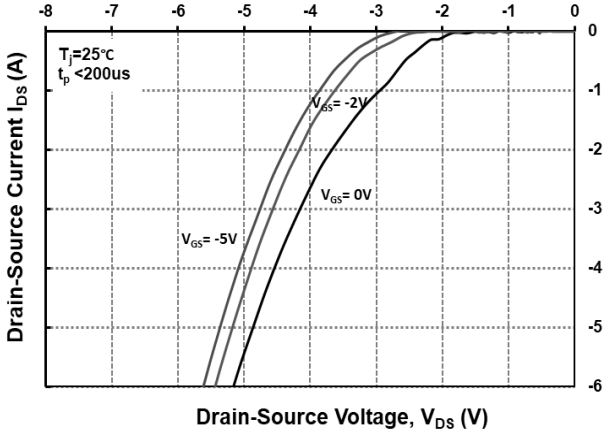


Fig 10. Body Diode Characteristics @ 175°C

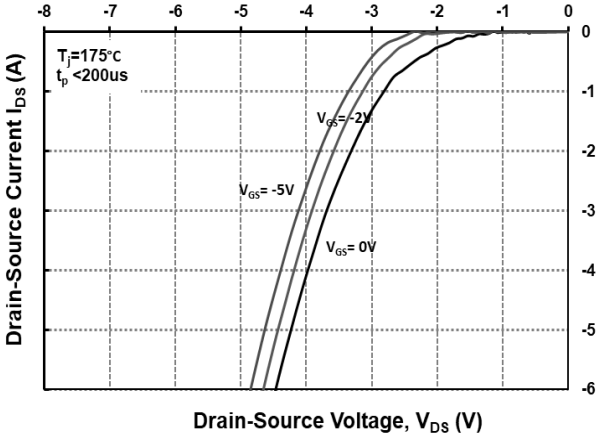


Fig 11. Threshold Voltage vs. Temperature

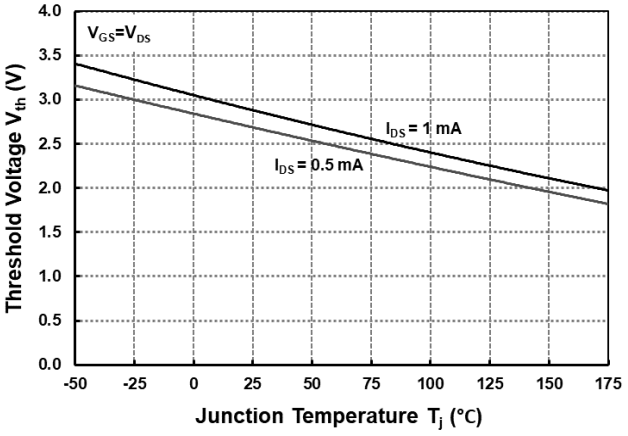
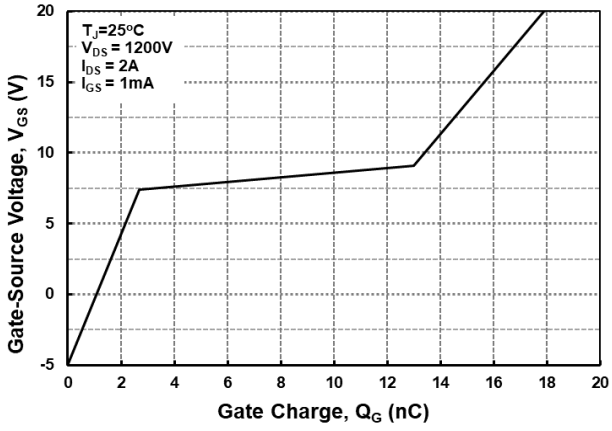


Fig 12. Gate Charge Characteristics



Typical Performance

Fig 13. 3rd Quadrant Characteristics @ -55°C

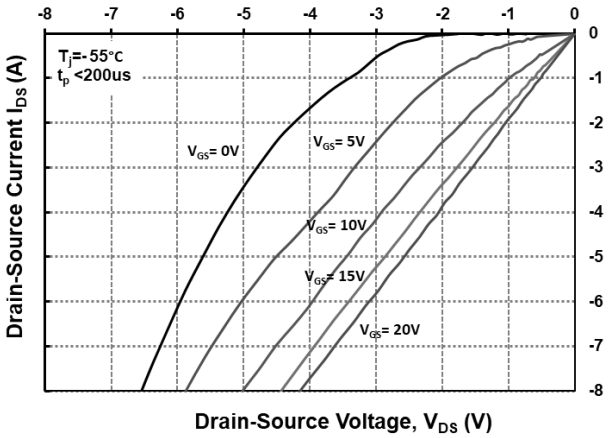


Fig 14. 3rd Quadrant Characteristics @ 25°C

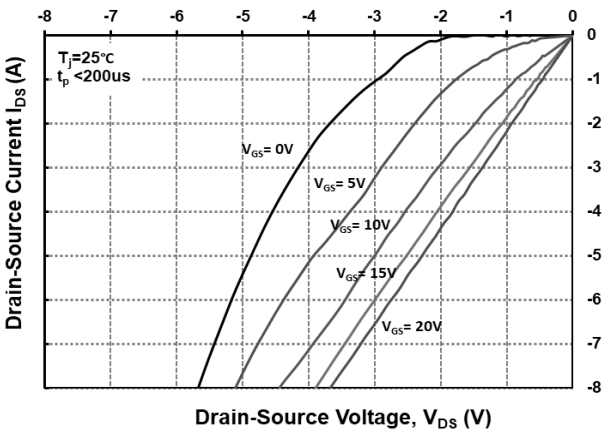


Fig 15. 3rd Quadrant Characteristics @ 175°C

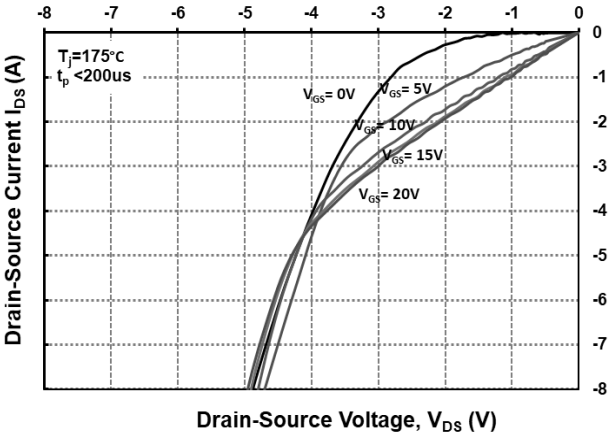


Fig 16. Output Capacitor Stored Energy

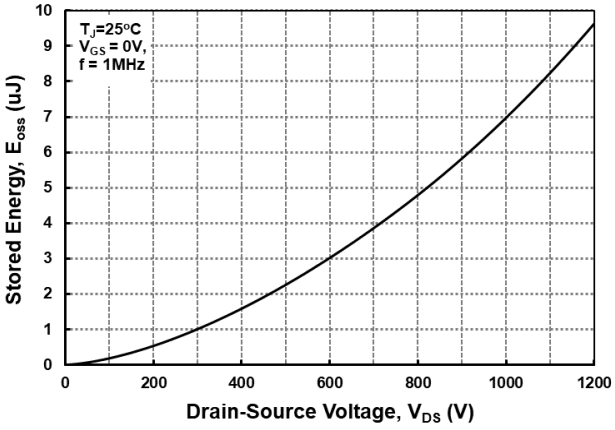


Fig 17. Capacitances vs. Drain-Source Voltage (0-200V)

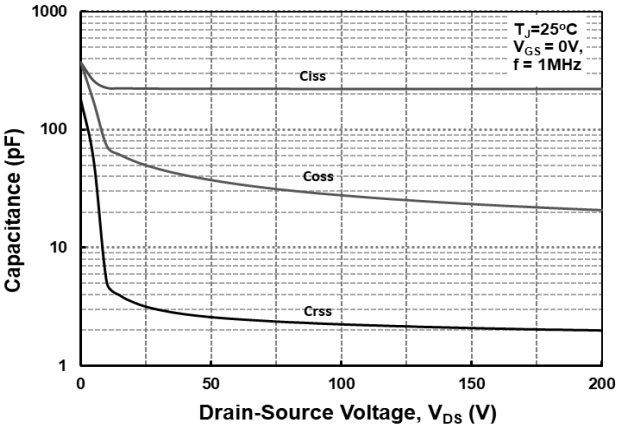
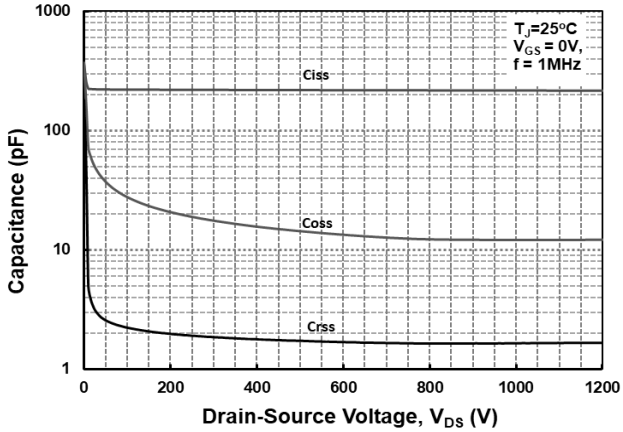


Fig 18. Capacitances vs. Drain-Source Voltage (0-1200V)



Typical Performance

Fig 19. Continuous Drain Current Derating vs. Case Temperature

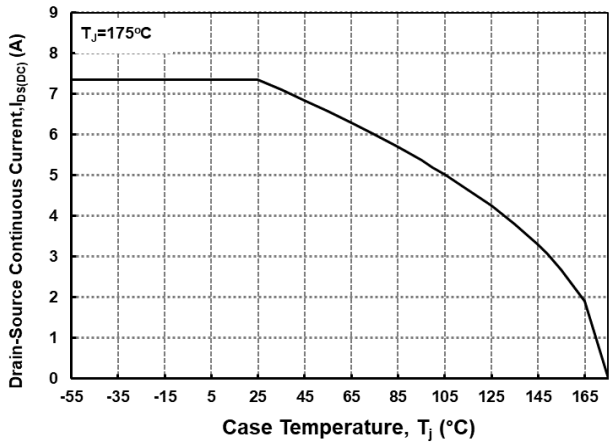


Fig 20. Maximum Power Dissipation Derating vs. Case Temperature

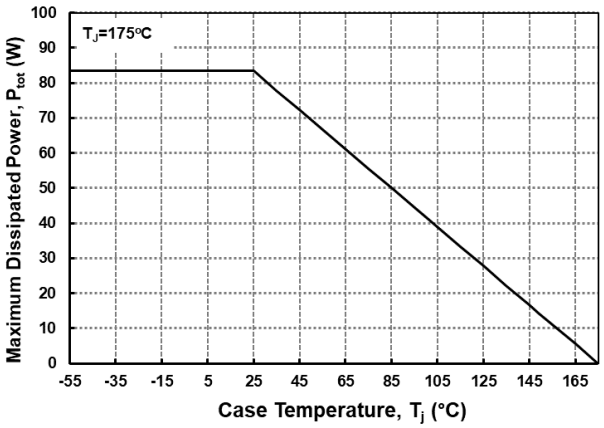


Fig 21. Transient Thermal Impedance (Junction-Case)

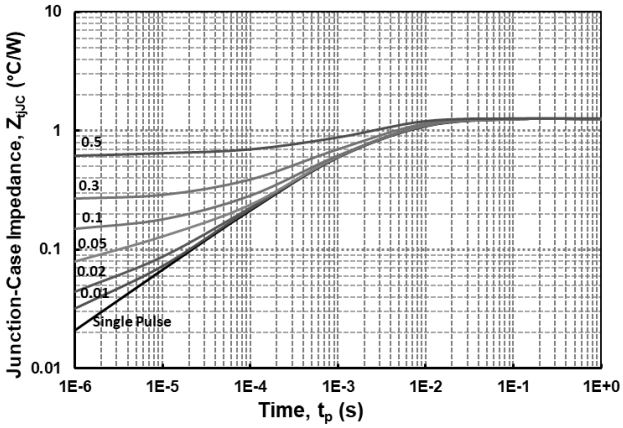


Fig 22. Safe Operating Area

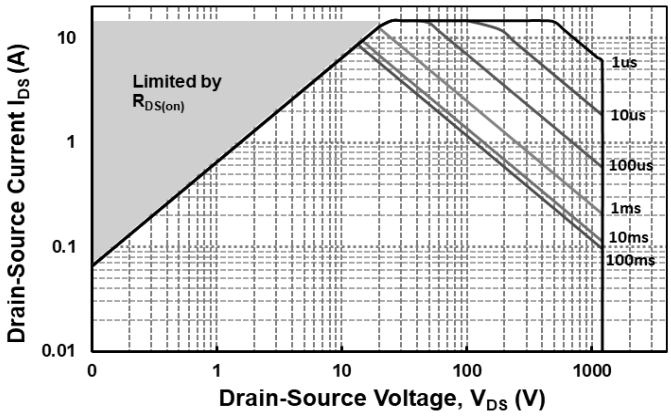


Fig 23. Clamped Inductive Switching Energy vs Drain Current (V_{DD} = 1200V)

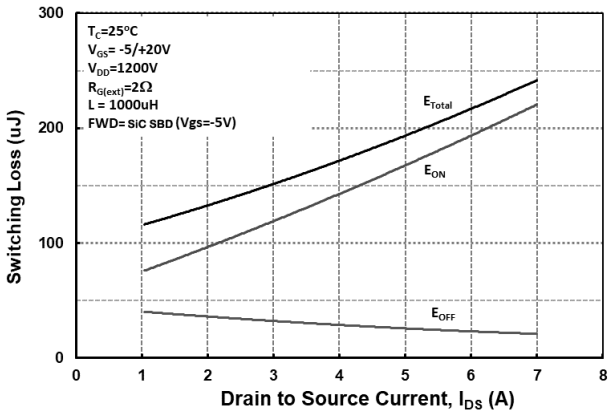
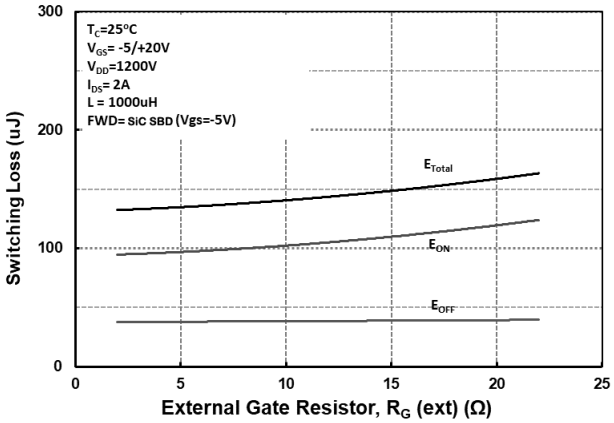


Fig 24. Clamped Inductive Switching Energy vs External Gate Resistor $R_{G(ext)}$



Typical Performance

Fig 25. Switching Times vs Drain Current (V_{DD} = 1200V)

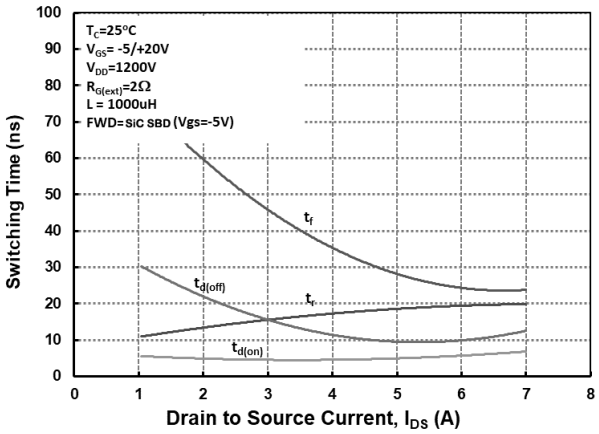
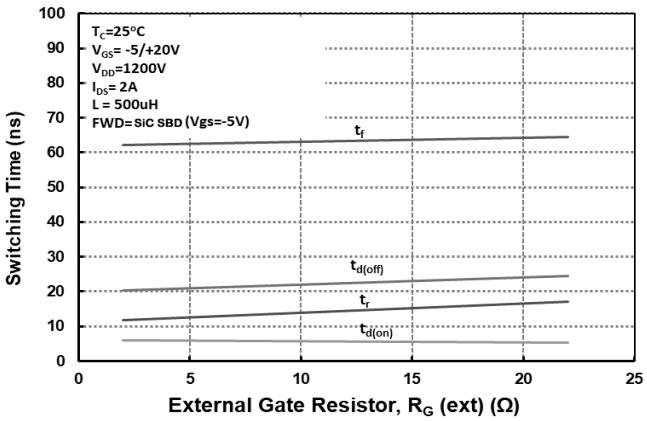


Fig 26. Switching Times vs External Gate Resistor $R_{G(ext)}$



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